

10BQ100 SCHOTTKY RECTIFIER

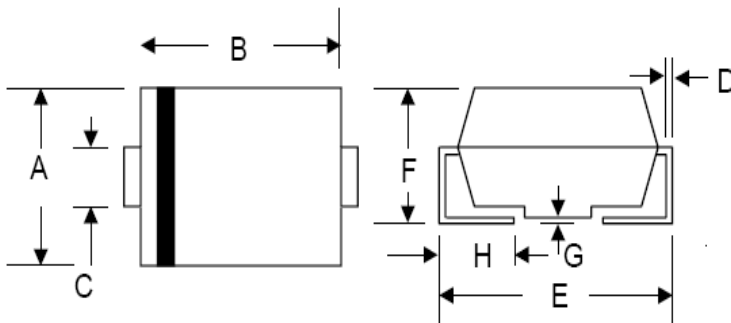
Applications:

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Features:

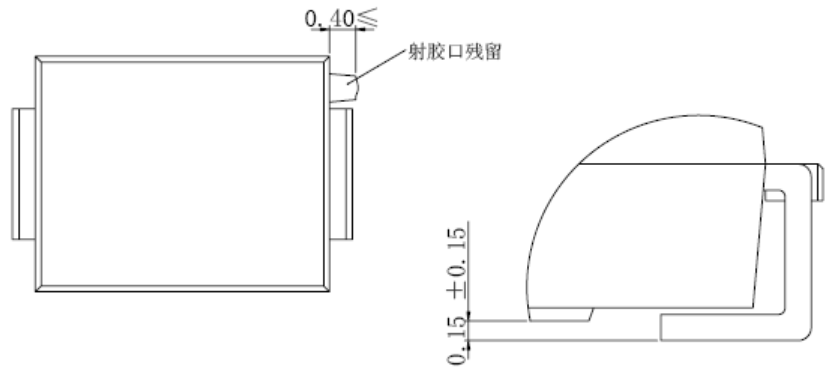
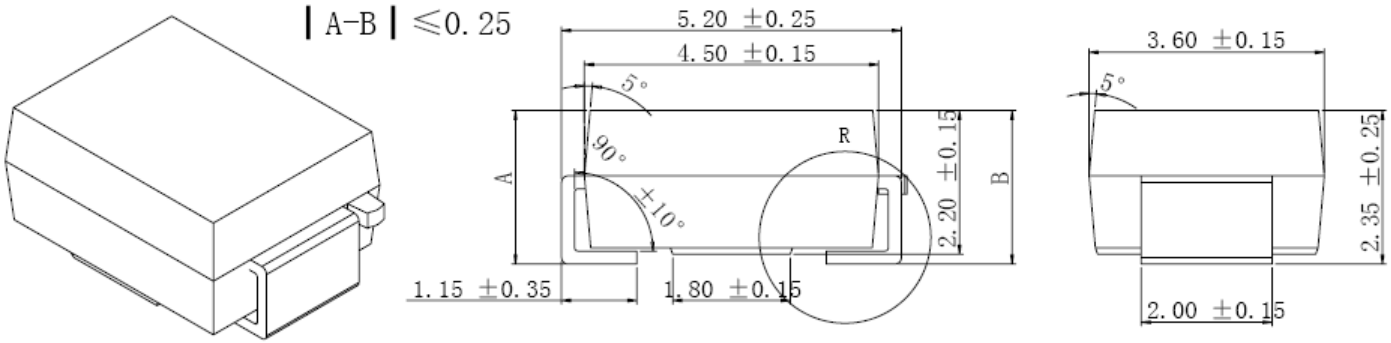
- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm



SMB/DO-214AA				
Dim	Min	Max	Min	Max
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.2	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
			in mm	In inch

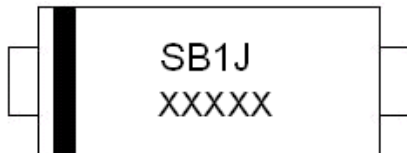
OPTION 1



OPTION 2(JK)

SMB

Marking Diagram:



Where XXXXX is YYWWL

SB1J = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
10BQ100	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=152C$, rectangular wave form	1.0	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	45	A



Electrical Characteristics:

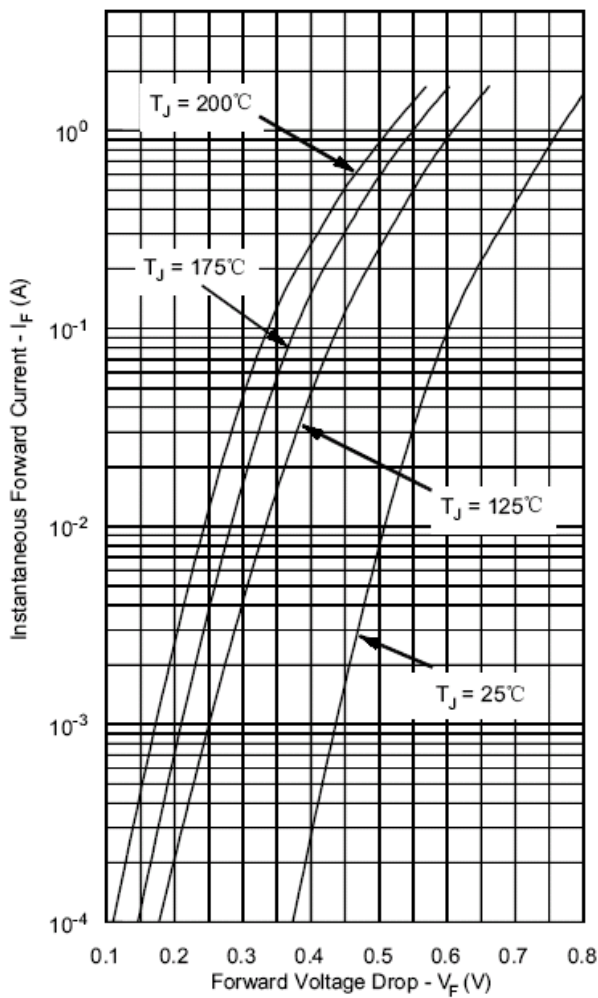
Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 1 A, Pulse, T _J = 25 °C @ 2 A, Pulse, T _J = 25 °C	0.78 0.89	V
	V _{F2}	@ 1 A, Pulse, T _J = 125 °C @ 2 A, Pulse, T _J = 125 °C	0.62 0.72	V
Reverse Current *	I _{R1}	@V _R = rated V _R , Pulse, T _J = 25 °C	0.5	mA
	I _{R2}	@V _R = rated V _R , Pulse, T _J = 125 °C	1	mA
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	42	PF
Typical Series Inductance	L _S	Measured lead to lead 5 mm from package body	2.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300μs, Duty Cycle < 2%

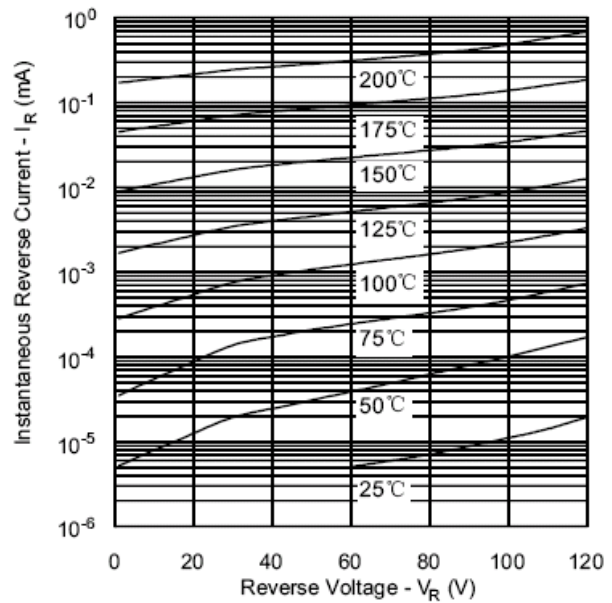
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Lead	R _{θJL}	DC operation	36	°C/W
Approximate Weight	wt	-	0.68	g
Case Style	SMB			

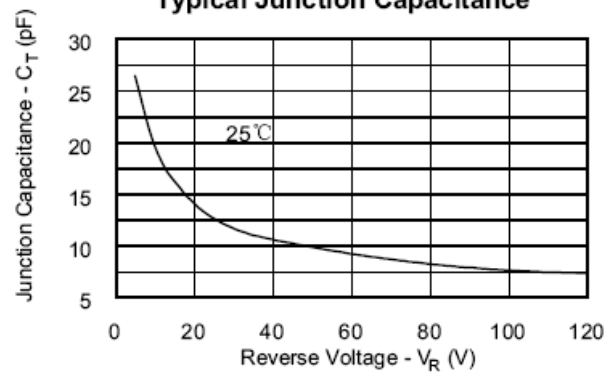
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





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